

FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT			ATTY DOCKET NO. 536-009.028		SERIAL NO. To be assigned 10/581127		
			APPLICANT: B. HEINEMANN et al.				
			FILING DATE: Herewith		ART UNIT: To be assigned		
UNITED STATES PATENT DOCUMENTS							
EXAM. INITIAL		DOCUMENT NUMBER	DATE	INVENTOR/ASSIGNEE	CLASS	FILING DATE IF APPROPRIATE	
/DN/		2005/0023642	Feb. 03, 2005	Heinemann et al.			
		2003/0146477	Aug. 07, 2003	Krutsick			
		2003/0146468	Aug. 07, 2003	Gris et al.			
		2002/0168829	Nov. 14, 2002	Bock et al.			
/DN/		2003/0162360	Aug. 28, 2003	Beasom			
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		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	TRANSLATION YES/NO	
/DN/		EP 0 746 038	Dec. 19, 2001	EP			
/DN/		2000188296	July 04, 2000	JP			
/DN/		2000269350	Sept. 29, 2000	JP			
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/DN/	1	M. C. Wilson et al., "Process HJ: A 30 GHz NPN and 20 GHz PNP complementary bipolar process for high linearity RF circuits," IEEE BCTM 9.4, 1998, pp.164-167.					
/DN/	2	D. Knoll et al., "A flexible, low-cost, high performance SiGe:C BiCMOS process with a one-mask HBT module," IEEE, 2002.					
/DN/	3	B. Heinemann et al., "Novel collector design for high-speed SiGe:C HBTs," IEEE, 2002.					
/DN/	4	D. V. Singh et al., "Novel epitaxial p-Si/n-Si _{1-x} C _x /p-Si heterojunction bipolar transistors," IEEE, 2000.					
/DN/	5	B. El-Kareh et al., "A 5V complementary -SiGe BiCMOS technology for high-speed precision analog circuits." date unknown					
/DN/	6	D. V. Singh et al., "Effect of band alignment and density of states on the collector current in p-Si/n-Si _{1-x} C _x /p-Si HBTs," IEEE Transactions on Electron Devices, Vol. 50, No. 2, February 2003, pp. 425-32.					
Examiner (To be assigned)				Date:			

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/DN/	2003/0219952	Nov. 27, 2003	Fujimaki			
/DN/	6,222,250	April 24, 2001	Gomi			
/DN/	4,719,185	Jan. 12, 1988	Goth			

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/DN/	7	Y. Chyan et al., "A 50-GHz 0.25 μ m implanted-base high-energy implanted-collector complementary modular BiCMOS (HEICBiC) technology for low-power wireless-communication VLSIs," IEEE BCTM 7.3, 1998, pp. 128-131.
/DN/	8	D. L. Harame et al., "55 GHz polysilicon-emitter graded SiGe-base PNP transistors," 1991, p. 71.
/DN/	9	T. Onai et al., "Self-aligned complementary bipolar technology for low-power dissipation and ultra-high-speed LSIs," IEEE Transactions on Electron Devices, Vol. 42, No. 3, March 1995, pp. 413-418.
/DN/	10	S. J. Jeng et al., "A 210-GHz fr SiGe HBT with a non-self-aligned structure," IEEE Electron Device Letters, Vol. 22, No. 11, November 2001.
/DN/	11	J. D. Cressler et al., "A high-speed complementary silicon bipolar technology with 12-fJ power-delay product," IEEE Electron Device Letters, Vol. 14, No. 11, November 1993, pp. 523-526.
/DN/	12	W. Klein et al., "75 GHz bipolar production technology for the 21st century," pp. 88-94. dateunknown

Examiner (To be assigned)	/David Nhu/	Date:	06/06/2010
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